

## PRODUCT / PROCESS CHANGE INFORMATION

### 1. PCI basic data

1.1 Company		STMicroelectronics International N.V
1.2 PCI No.		ADG/18/10949
1.3 Title of PCI		STD5N60DM2 Datasheet UPDATE
1.4 Product Category		Power MOSFET
1.5 Issue date		2018-06-11

### 2. PCI Team

2.1 Contact supplier	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Maurizio GIUDICE
2.1.2 Marketing Manager	Anna MOTTESE
2.1.3 Quality Manager	Vincenzo MILITANO

### 3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
General Product & Design	Modification of datasheet : Errata/error fix	ASE-WEIHAI (China)

### 4. Description of change

	Old	New
4.1 Description	IAR=1.7A, Ciss=375pF, Coss=13pF, Crss=0.3pF, Coss eq.=21pF, RG=6.5?, QG=8.6nC, Qgs=2nC, Qgd=5.2nC.	IAR=1A, Ciss=214pF, Coss=12pF, Crss=3.5pF, Coss eq.=21pF, RG=6.5?, QG=5.3nC, Qgs=1.4nC, Qgd=2.7nC.
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	no impact	

### 5. Reason / motivation for change

5.1 Motivation	Improve Service to Customer.
5.2 Customer Benefit	SERVICE IMPROVEMENT

### 6. Marking of parts / traceability of change

6.1 Description	by traceability code
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### 7. Timing / schedule

7.1 Date of qualification results	2018-06-07
7.2 Intended start of delivery	2018-07-07
7.3 Qualification sample available?	Not Applicable

### 8. Qualification / Validation

8.1 Description		
8.2 Qualification report and qualification results	In progress	Issue Date

### 9. Attachments (additional documentations)

10949 Public product.pdf
10949 STD5N60DM2 - Datasheet UPDATE.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	STD5N60DM2	

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Automotive and Discrete Group (ADG)  
Power Transistor Division  
**HV Business Unit**

**STD5N60DM2 datasheet UPDATE**

Dear Customer,

Please be informed that, we are going to modify the datasheet of **STD5N60DM2** according to the following tables:

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value		Unit
		Current	NEW	
I <sub>AR</sub> (1)	Avalanche current, repetitive or not repetitive	1.7	1	A

**Notes:**

(1) Pulse width limited by T<sub>jmax</sub>.

**Table 6: Dynamic**

Symbol	Parameter	Value	Min.	Typ.		Max.	Unit
				Current	NEW		
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 100 V, f = 1 MHz, V <sub>GS</sub> = 0 V	-	375	214	-	pF
C <sub>oss</sub>	Output capacitance		-	13	12	-	
C <sub>rss</sub>	Reverse transfer capacitance		-	0.3	3.5	-	
C <sub>oss eq.</sub> (1)	Equivalent output capacitance	V <sub>DS</sub> = 0 to 480 V, V <sub>GS</sub> = 0 V	-	21	21	-	pF
R <sub>G</sub>	Intrinsic gate resistance	f = 1 MHz, I <sub>D</sub> = 0 A	-	6.5	6.5	-	Ω
Q <sub>G</sub>	Total gate charge	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 3.5 A, V <sub>GS</sub> = 0 to 10 V (see <a href="#">Figure 15: "Test circuit for gate charge behavior"</a> )	-	8.6	5.3	-	nC
Q <sub>gs</sub>	Gate-source charge		-	2	1.4	-	
Q <sub>gd</sub>	Gate-drain charge		-	5.2	2.7	-	

**Notes:**

(1) C<sub>oss eq.</sub> is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>.

The change will also have an impact on the related curves.

Please contact us for more information.

Sincerely Yours.



## Public Products List

Public Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

**PCI Title :** STD5N60DM2 Datasheet UPDATE

**PCI Reference :** ADG/18/10949

**Subject :** Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STD5N60DM2		
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